Probing the mechanism of infrared resonant desorption of hydrogen from Si(111): anharmonicity and energy pooling\textsuperscript{1} ZHIHENG LIU, LEONARD FELDMAN, NORMAN TOLK, Vanderbilt University, ZHENYU ZHANG, Oak Ridge National Laboratory, PHILIP COHEN, University of Minnesota — Desorption of hydrogen from a Si(111) surface by resonant infrared excitation of the Si–H vibrational stretch mode requires vibrational ladder climbing of a Si–H bond to a high level leading to associative desorption. We report recent experiments probing the mechanism of ladder climbing. H\textsubscript{2} desorption is observed when the excitation linewidths are narrower than the anharmonicity of the Si–H bond, favoring energy pooling over multiphoton absorption. The resonance width of H\textsubscript{2} desorption with an excitation linewidth of 8.7 cm\textsuperscript{-1} is measured to be 39 cm\textsuperscript{-1}, opening a new opportunity for site-selective modification on the Si(111) surface. The desorption yield decreases when the sample temperature increases, consistent with an energy pooling process.

\textsuperscript{1}This work is funded by DARPA/SPAWAR grant N66001-04-1-8924, DOE grant ER45781, and NSF grant DMR-0306239.

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Date submitted: 20 Nov 2006

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